

SOT-23 Formed SMD Package

**BSR20
BSR20A**

SILICON P-N-P HIGH-VOLTAGE TRANSISTORS

P-N-P high-voltage small-signal transistors

Marking

BSR20 = T35

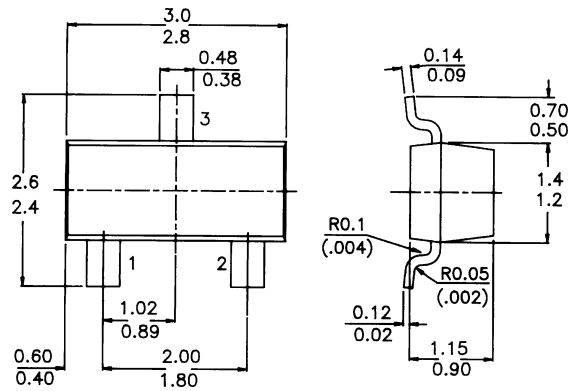
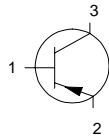
BSR20A = T36

PACKAGE OUTLINE DETAILS

ALL DIMENSIONS IN mm

Pin configuration

- 1 = BASE
- 2 = EMITTER
- 3 = COLLECTOR



ABSOLUTE MAXIMUM RATINGS

	BSR20 BSR20A	
Collector-base voltage (open emitter)	$-V_{CB0}$ max.	130 160 V
Collector-emitter voltage (open base)	$-V_{CE0}$ max.	120 150 V
Collector current	$-I_C$ max.	600 600 mA
Total power dissipation up to $T_{amb} = 25\text{ }^\circ\text{C}$	P_{tot} max.	250 250 mW
Junction temperature	T_j max.	150 150 $^\circ\text{C}$
Collector-emitter saturation voltage	V_{CEsat} max.	0.5 0.5 V
$I_C = 50\text{ mA}; I_B = 5\text{ mA}$		
D.C. current gain	h_{FE} min.	40 60
$I_C = 10\text{ mA}; V_{CE} = -5\text{ V}$	h_{FE} max.	180 240

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RATINGS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

Limiting values

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Collector-base voltage (open emitter)	$-V_{CB0}$	max. 130	160 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max. 120	150 V
Emitter-base voltage (open collector)	$-V_{EB0}$	max. 5	V
Collector current	$-I_C$	max. 600	mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot}	max. 250	mW
Junction temperature	T_j	max. 150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL RESISTANCE

From junction to ambient	$R_{th\ j-a}$	=	500	K/W
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CHARACTERISTICS

$T_{amb} = 25^\circ\text{C}$ unless otherwise specified

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Collector cut-off current			
$I_E = 0; -V_{CB} = 100\text{ V}$	$-I_{CB0}$	max. 100	nA
$I_E = 0; -V_{CB} = 120\text{ V}$	$-I_{CB0}$	max. 50	nA
$I_E = 0; -V_{CB} = 100\text{ V}; T_{amb} = 100^\circ\text{C}$	$-I_{CB0}$	max. 100	mA
$I_E = 0; -V_{CB} = 120\text{ V}; T_{amb} = 100^\circ\text{C}$	$-I_{CB0}$	max. 50	mA
Emitter cut-off current			
$I_C = 0; -V_{EB} = 4,0\text{ V}$	$-I_{EB0}$	max. 50	50 nA
Breakdown voltages			
$I_C = 1,0\text{ mA}; I_B = 0$	$-V_{(BR)CE0}$	min. 120	150 V
$I_C = 100\text{ mA}; I_E = 0$	$-V_{(BR)CB0}$	min. 130	160 V
$I_C = 0; I_E = 10\text{ mA}$	$-V_{(BR)EB0}$	min. 5,0	5,0 V
Saturation voltages			
$-I_C = 10\text{ mA}; -I_B = 1,0\text{ mA}$	$-V_{CEsat}$	max. 0,2	0,2 V
	$-V_{BEsat}$	max. 1,0	1,0 V
$-I_C = 50\text{ mA}; -I_B = 5,0\text{ mA}$	$-V_{CEsat}$	max. 0,5	0,5 V
	$-V_{BEsat}$	max. 1,0	1,0 V
D.C. current gain			
$I_C = 1,0\text{ mA}; -V_{CE} = 5\text{ V}$	h_{FE}	min. 30	50
$I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$	h_{FE}	min. 40	60
		max. 180	240
$I_C = 50\text{ mA}; -V_{CE} = 5\text{ V}$	h_{FE}	min. 40	50
Output capacitance at $f = 1\text{ MHz}$			
$I_E = 0; -V_{CB} = 10\text{ V}$	C_o	max. 6	6 pF

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Transition frequency at $f = 100$ MHz $-I_C = 10$ mA; $-V_{CE} = 10$ V	f_T	min. 100	100 MHz
		max. 400	300 MHz
Noise figure at $R_S = 1$ kW $I_C = 250$ mA; $-V_{CE} = 5$ V; $f = 10$ Hz to 15,7 kHz	F	max. 8	8 dB
Small Signal Current Gain $-V_{CE} = 10$ V; $-I_C = 1$ mA; $f = 1$ KHz	h_{fe}	min. 30	40
		max. 200	200

Disclaimer

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